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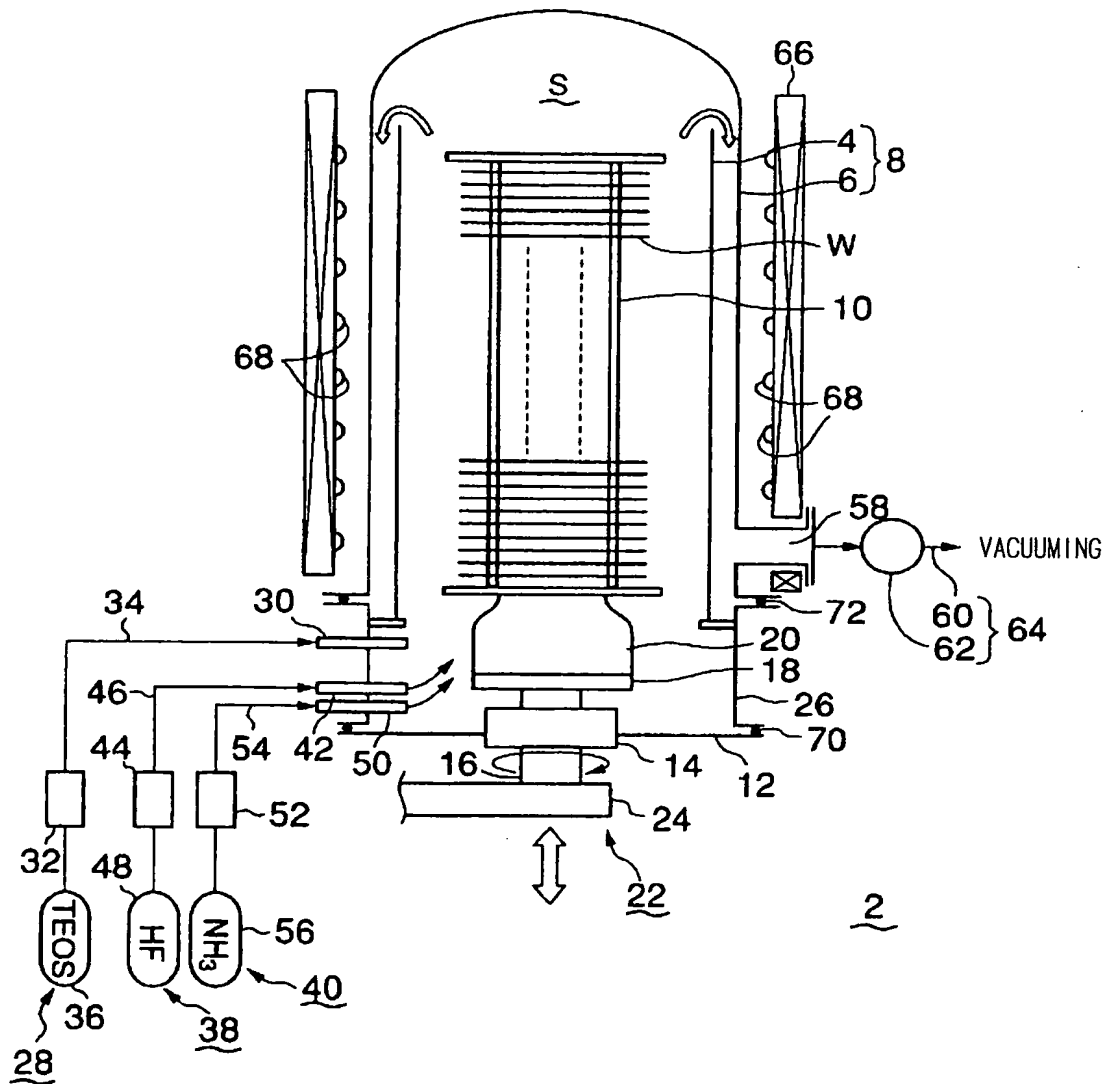


FIG. 1

ETCHING RATE OF SILICON OXIDE FILM FORMED BY TEOS			ETCHING RATE OF QUARTZ MATERIAL			EVALUATION
	TEMPERATURE [°C]	PRESSURE [Torr]	HF [sccm]	NH ₃ [sccm]	[nm/min]	[nm/min]
METHOD ACCORDING TO PRESENT INVENTION	300	400	182	1820	0.6	15.9
	300	400	1000	1000	26.8	69.1
	300	400	1820	182	96.6	196.6
CONVENTIONAL METHOD	300	400	1820	0	0.4	170.1
						△
						○
						○
						×

FIG. 2

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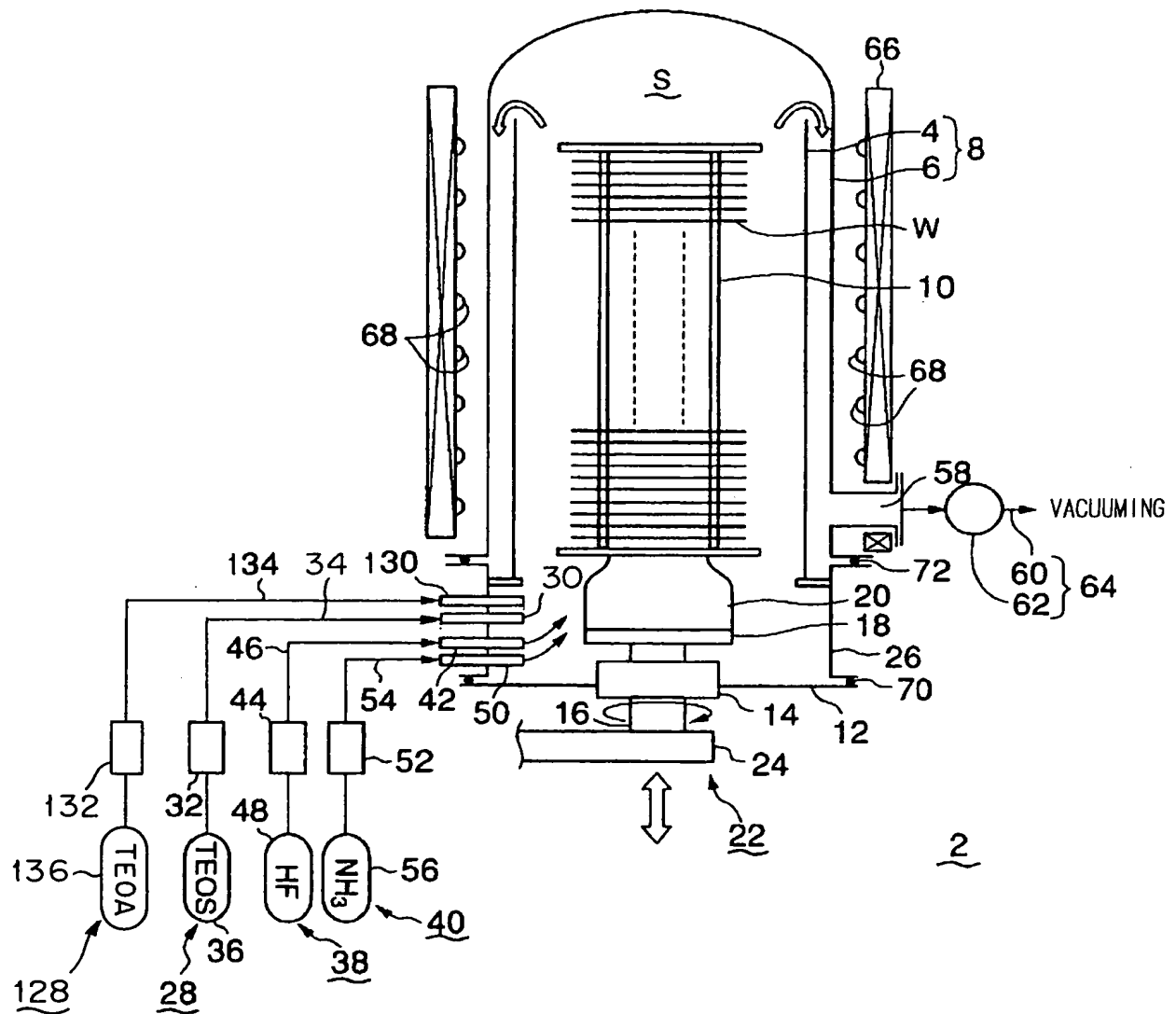


FIG. 3

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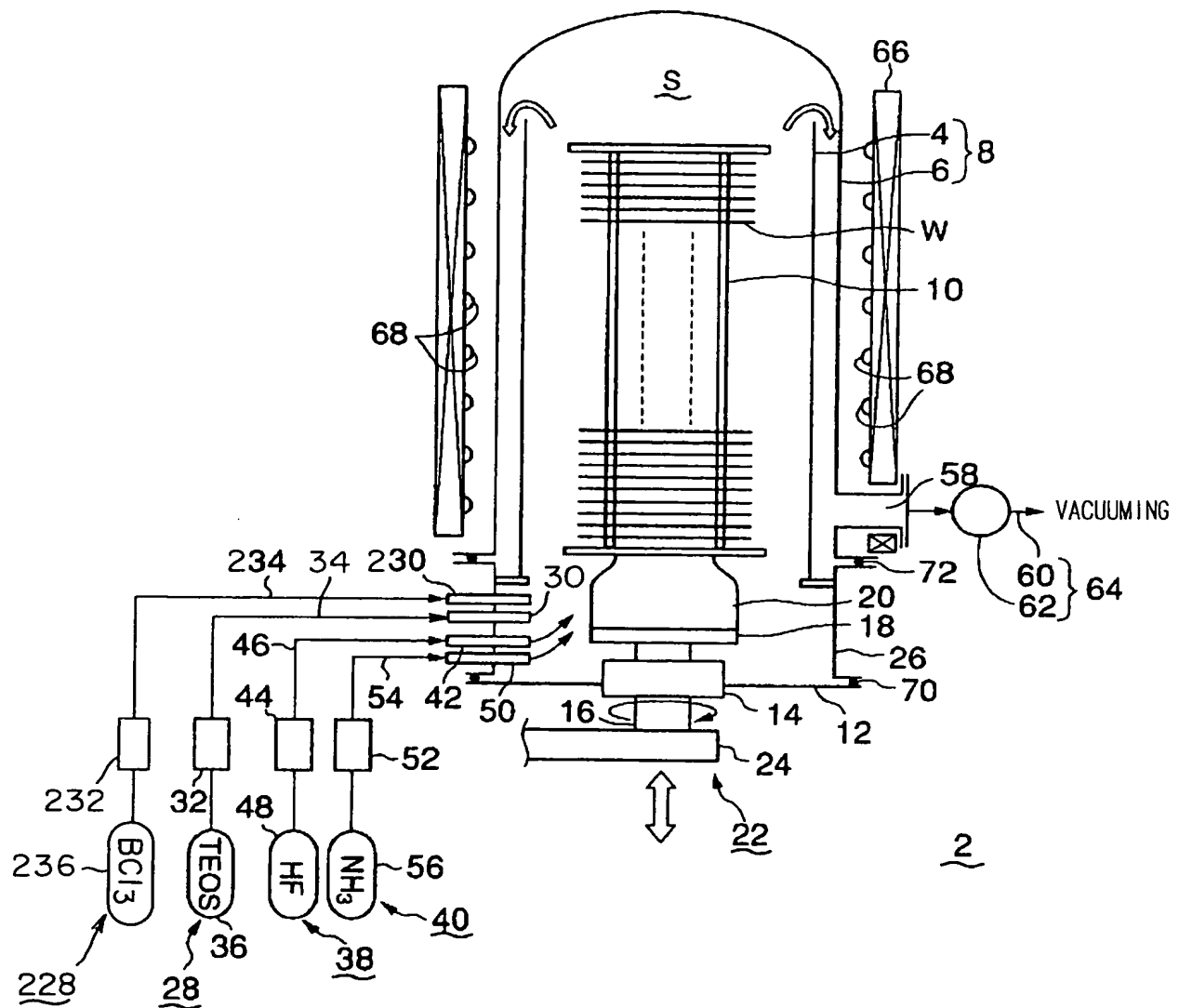


FIG. 4